

Amendments to the Specification:

Please replace the paragraph bridging pages 1 and 2 with the following amended paragraph:

There are two types of the EL light emitting device, i.e. an active matrix type and a passive matrix type. [[there]] There has been development of both types actively carried out. At present, the active matrix type EL light emitting device is particularly noted. The active matrix type EL light emitting device is characterized in that a thin film transistor (hereinafter referred to as TFT) is provided for each of pixels of a pixel section to control an amount of current flowing in an EL element.

Please replace the paragraph beginning at page 4, line 1, with the following amended paragraph:

Moreover, in the above combination of 2), with the combination of bromine trichloride (BrCl_3) gas and chlorine (Cl_2) gas, an aluminum film is etched and a tungsten film is not. Furthermore, with the combination of chlorine (Cl_2) gas and carbon tetrafluoride (CF_4) gas, a tungsten film is [[etched]] etched, but an aluminum film is not. In this way, selectivity can be provided for both of the conductive films.

Please replace the paragraph beginning at page 18, line 11, with the following amended paragraph:

Since the bank 384 is an insulating film, the deposition must be carried out carefully not to cause electrostatic discharge. In the embodiment 1, carbon powder or pigment is added into the insulating film to be the material of the bank 384 to lower resistivity and to prevent generation of static electricity. At this time, the amount of the

carbon powder or pigment to be added can be adjusted so that the ~~resitivity~~ resistivity becomes from 1×10^6 to $1\times10^{12}\Omega\text{m}$ (preferably from 1×10^8 to $1\times10^{10}\Omega\text{m}$).

Please replace the paragraph beginning at page 19, line 8, with the following amended paragraph:

In the embodiment 1, polythiophene (PEDOT) is first formed to a thickness of 20 nm as a hole injecting layer. Furthermore, as a light emitting layer that emits white light, polyvinyl carbazole (PVK) is formed to a thickness of 80nm. The ~~polythiophene~~ polythiophene can be applied in being dissolved in water, and the polyvinyl carbazole can be applied in being dissolved in 1,2-dichloromethane. The hole injecting layer and the light emitting layer after being applied are heat treated within a temperature range (typically from 80 to 120°C) that causes no breakage of the EL layer, and are obtained as a thin film by making solvent volatilize.

Please replace the paragraph bridging pages 24 and 25 with the following amended paragraph:

The above configuration can be easily realized by manufacturing the TFT in accordance with the manufacturing steps shown in FIG. 2A through FIG. 4B. Although only constitutions of the pixel portion and the driving circuit portion are shown in the embodiment 1, logic circuits such as a signal separation circuit, a D/A converter, an operational amplifier, and a gamma compensation circuit can be formed on the same substrate in accordance with the manufacturing method of the present ~~invention~~ invention. Furthermore, it is considered that memories and a micro processor and the like can be also formed.

Please replace the paragraph bridging pages 30 and 31 with the following amended paragraph:

Here, a view of a pixel portion seen from above is shown in FIG. 11. In addition, a view of a cross section ~~takeng~~ taken along line A-A' in FIG. 11 is shown in FIG. 12A, a cross section taken along line B-B' is shown in FIG. 12B, and a cross section taken along line C-C' is shown in FIG. 12C. FIGS. 12A, 12B, and 12C show cross section structures of a switching TFT, current controlling TFT, and a holding capacitor, respectively. The pixel portion shown here can be formed with reference to the manufacturing steps shown in FIG. 2A through FIG. 4B.